



VDRM

T(AV)

Iтsм dV/dt*

dl/dt

KEY PARAMETERS

2200V

5050A

72500A

2000V/µs

500A/µs

* Higher dV/dt selections are available on request



Replaces DS5925-1

Phase Control Thyristor

DS5925-2	July 2022	(LN41921)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages Vdrm and Vrrm (V)	Conditions
DCR5050B22 DCR5050B20 DCR5050B18	2200 2000 1800	$T_{vj} = -40^{\circ}C \text{ to } 125^{\circ}C,$ IDRM = IRRM = 200mA, $VDRM, VRRM t_{P} = 10ms$ VDSM & VRSM = VDRM & VRRM + 100V respectively

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR5050B22

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

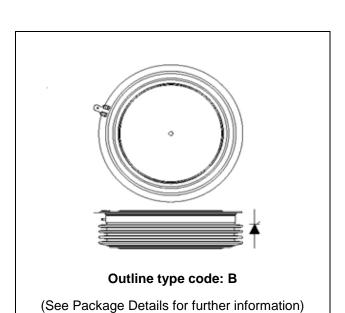


Fig. 1 Package outline

CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
Ιτ(Αν)	Mean on-state current	Half wave resistive load	5050	А
It(rms)	RMS value	-	7930	А
Гт	Continuous (direct) on-state current	-	6860	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, Tcase = 125°C	72.5	kA
l²t	I ² t for fusing	VR = 0	26.3	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Parameter Test Conditions		Min.	Max.	Units
	Thermal resistance - junction to case	Double side cooled	DC	-	7.0	°C/kW
Rth(j-c)			Anode DC	-	11.5	°C/kW
		Single side cooled	Cathode DC	-	18.1	°C/kW
Rth(c-h)	Thermal resistance - case to heatsink	Clamping force 76kN (with mounting compound)	Double side	-	1.4	°C/kW
			Single side	-	2.8	°C/kW
Tvj	Virtual junction temperature	Blocking Vdrm / Vrrm		-	125	°C
Tstg	Storage temperature range			-55	125	°C
Fm	Clamping force			68	84	kN

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Condition	IS	Min.	Max.	Units
Irrm/Idrm	Peak reverse and off-state current	At Vrrm/Vdrm, Tcase = 125°C		-	200	mA
Vтм	Instantaneous forward voltage	At 4000A peak, Tj = 125°C		1.05	1.15	V
dV/dt	Max. linear rate of rise of off-state voltage	То 67% V _{DRM} , Тј = 125°С, g	ate open	-	2000	V/µs
dl/dt	Rate of rise of on-state current	From 67% VDRM to 2x $I_{T(AV)}$ Gate source 30V, 10 Ω	Repetitive 50Hz	-	250	A/µs
avat		$tr < 0.5\mu s, T_j = 125^{\circ}C$	Non-repetitive	-	500	A/µs
	Threshold voltage - Low level	500A to 2700A at Tcase = 125°C		-	0.72	V
V τ(το)	Threshold voltage - High level	2700A to 7000A at Tcase = 1	00A at T _{case} = 125°C		0.88	V
	On-state slope resistance - low level	500A to 2700A at Tcase = 125°C		-	0.13	mΩ
ľΤ	On-state slope resistance - High level	vel 2700A to 7000A at T _{case} = 125°C		-	0.07	mΩ
tgd	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10Ω tr = 0.5µs, Tj = 25°C		0.5	1.5	μs
tq	Turn-off time	$T_{j} = 125^{\circ}C, V_{R} = 200V, dI/dt = 1A/\mu s,$ $dV_{DR}/dt = 20V/\mu s \text{ linear}$		50	150	μs
Qs	Stored charge $I_T = 2000A$, $T_j = 125^{\circ}C$, $dI/dt = 1A/\mu s$		470	1580	μC	
Irr	Reverse recovery current	Vr(peak) ~ 1300V, Vrm ~ 900V		20	36	А
lı.	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	А
Ін	Holding current	Тј = 25°С, R _{G-} к = ∞, Iтм = 50	0A, I⊤ = 5A	-	300	mA

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GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Vgт	Gate trigger voltage	Vdrm = 5V, Tcase = 25°C	1.5	V
Vgd	Gate non-trigger voltage	At 50% VDRM, Tcase = 125°C	0.4	V
Іст	Gate trigger current	VDRM = 5V, Tcase = 25°C	250	mA
Igd	Gate non-trigger current	At 50% Vdrm, Tcase = 125°C	10	mA

CURVES

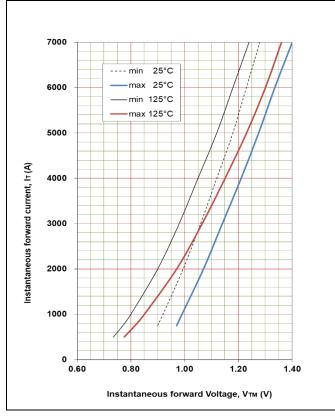


Fig. 2 Maximum & minimum on-state characteristics

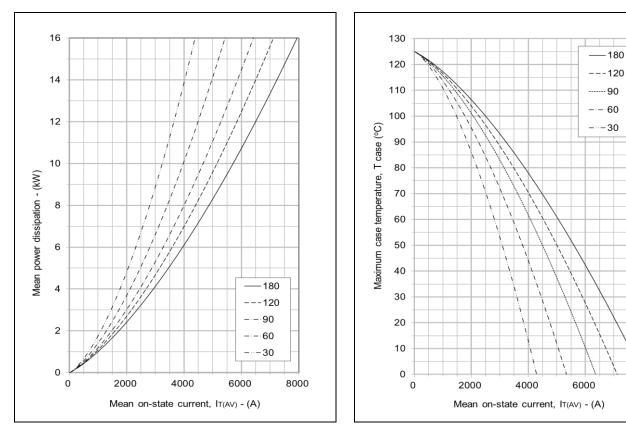
VTM EQUATION

 $V_{TM} = A + B.ln(I_T) + C.I_T + D.\sqrt{I_T}$

Where A = 0.697062B = -0.020802C = 0.000015D = 0.008913These values are valid for T_j = 125° C for I_T 500A to 7000A

DCR5050B22

8000



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Fig. 3 On-state power dissipation - sine wave

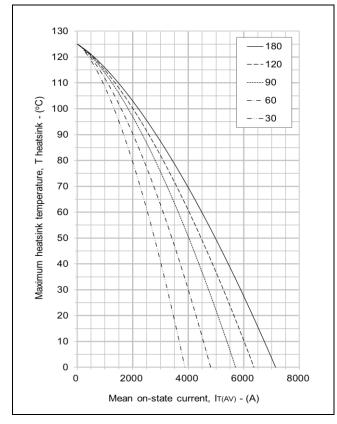


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

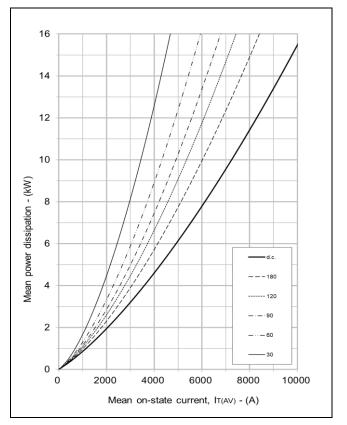


Fig. 6 On-state power dissipation - rectangular wave

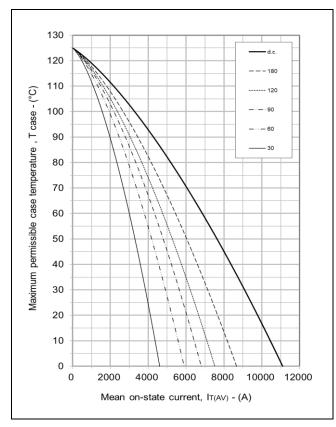
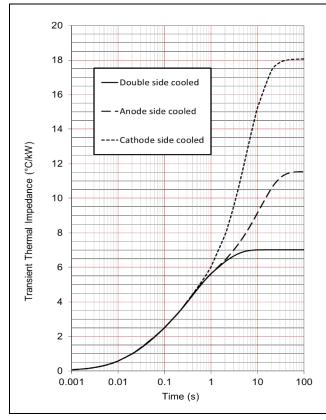


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



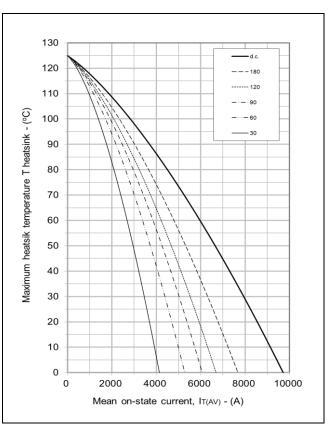


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side	Ri(°C/kW)	0.502	1.333	2.956	2.234
cooled	Ti(s)	0.014	0.055	0.331	1.691
Anode side	Ri(°C/kW)	1.304	3.138	1.186	5.914
cooled	Ti(s)	0.025	0.241	1.081	11.002
Cathode side	Ri(°C/kW)	1.262	2.622	13.360	0.830
cooled	Ti(s)	0.025	0.201	5.785	16.765

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

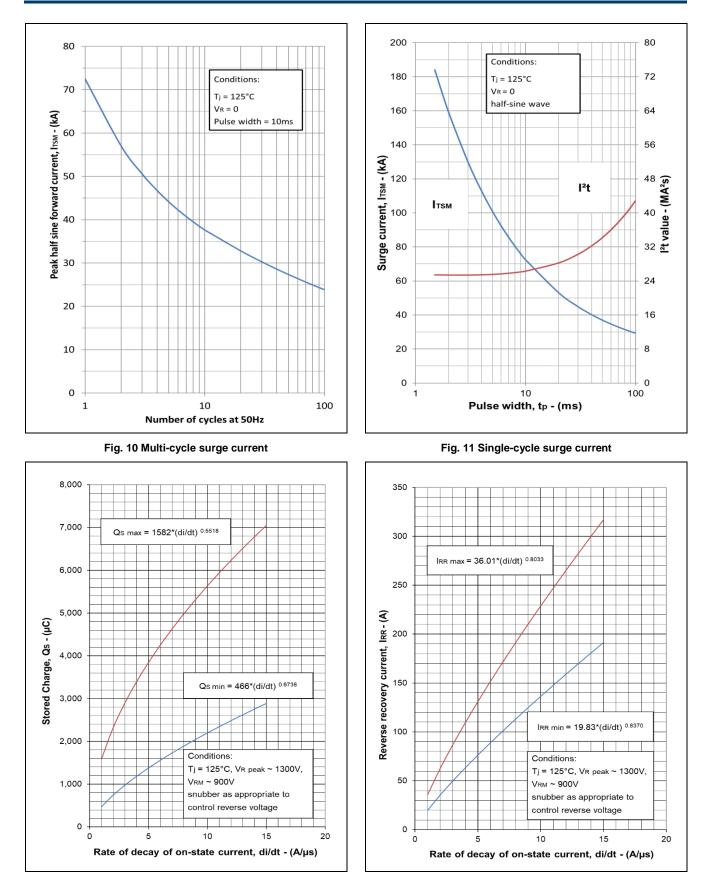
 $\Delta R_{th(j-c)}$ Conduction

Tables show the increments of thermal resistance R $_{\text{frij-ej}}$ when the device operates at conduction angles other than d.c.

	Double side co	oling		Anode Side Cooling		Ca	thode Side	d Cooling		
	$\Delta Z_{th}(z)$			$\Delta Z_{th}(z)$		$\Delta Z_{th}(z)$			ΔZ	_h (z)
θ°	sine.	rect.	θ°	sine.	rect.	θ°	sine.	rect.		
180	0.70	0.48	180	0.67	0.47	180	0.67	0.47		
120	0.80	0.68	120	0.77	0.66	120	0.77	0.66		
90	0.90	0.78	90	0.87	0.75	90	0.87	0.76		
60	1.00	0.89	60	0.95	0.86	60	0.95	0.86		
30	1.07	1.01	30	1.02	0.96	30	1.02	0.96		
15	1.10	1.07	15	1.05	1.02	15	1.05	1.02		

Fig. 9 Maximum (limit) transient thermal impedance – junction to case (degC/kW)

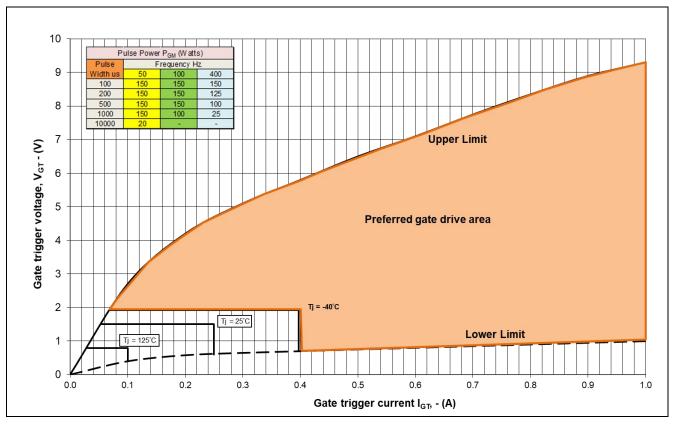
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Fig. 12 Reverse recovery charge

Fig. 13 Reverse recovery current



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Fig. 14 Gate characteristics

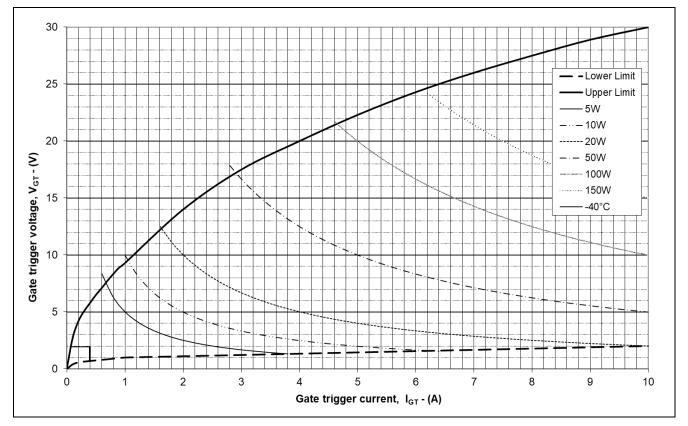


Fig. 15 Gate characteristics

PACKAGE DETAILS

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE

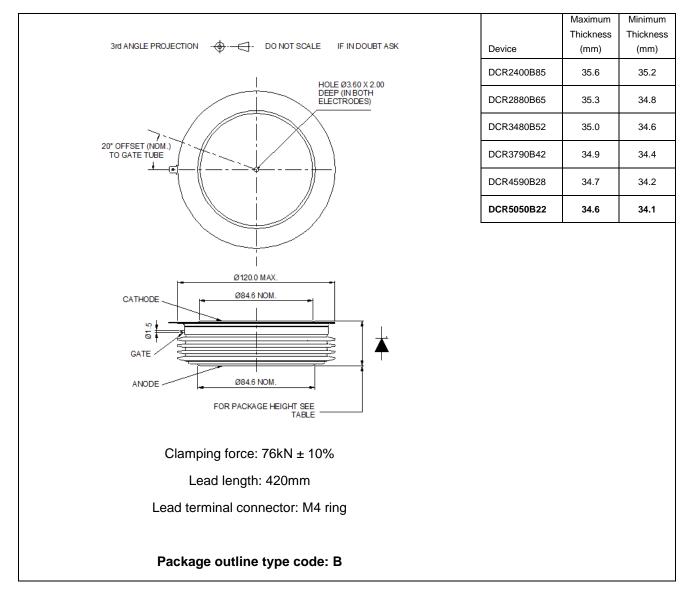


Fig. 16 Package outline

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